

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,858,502 B2
DATED : February 22, 2005
INVENTOR(S) : Jack Oon Chu et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1,

Line 23, "(HFMTs)" should read -- (HEMTs) --.

Column 2,

Line 27, "Si_{1-x}Ge_w" should read -- Si_{1-w}Ge_w --.

Column 12,

Line 19, "Si_{1-w}Ge_x" should read -- Si_{1-w}Ge_w --.

Column 13,

Line 29, "below the a channel" should read -- below a channel --.

Column 14,

Line 46, "layer fanned" should read -- layer formed above --.

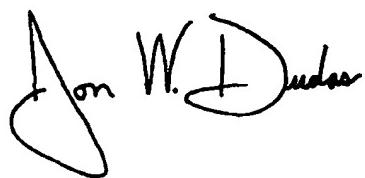
Line 49, "method of fanning" should read -- method of forming --.

Column 15,

Line 24, "dram electrode" should read -- drain electrode --.

Signed and Sealed this

Thirtieth Day of August, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office